Marie-Paule Besland

List of Publications by Year
in descending order

61	1,145	394421 19	434195 31
papers	citations	h-index	g-index

61	61	61	1660
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	A Leakyâ€Integrateâ€andâ€Fire Neuron Analog Realized with a Mott Insulator. Advanced Functional Materials, 2017, 27, 1604740.	14.9	186
2	Resistive Switching in Mott Insulators and Correlated Systems. Advanced Functional Materials, 2015, 25, 6287-6305.	14.9	130
3	Reactive ion etching of solâ€“gel-processed SnO2 transparent conducting oxide as a new material for organic light emitting diodes. Synthetic Metals, 2002, 127, 207-211.	3.9	42
4	TEM and XPS studies on CdS/CIGS interfaces. Journal of Physics and Chemistry of Solids, 2014, 75, 1279-1283.	4.0	41
5	Preparation and characterization of ZnS/CdS bi-layer for CdTe solar cell application. Journal of Physics and Chemistry of Solids, 2013, 74, 1879-1883.	4.0	39
6	Evidence for a new passivating indium rich phosphate prepared by ultraviolet/ozone oxidation of InP. Applied Physics Letters, 1991, 59, 1617-1619.	3.3	36
7	Electrical characterization of metal-oxide-InP tunnel diodes based on current-voltage, admittance and low frequency noise measurements. Solid-State Electronics, 1995, 38, 1035-1043.	1.4	36
8	Effect of RF sputtering power and vacuum annealing on the properties of AZO thin films prepared from ceramic target in confocal configuration. Materials Science in Semiconductor Processing, 2020, 118, 105217.	4.0	36
9	Different threshold and bipolar resistive switching mechanisms in reactively sputtered amorphous undoped and Cr-doped vanadium oxide thin films. Journal of Applied Physics, 2018, 123, .	2.5	33
10	Comparison of lanthanum substituted bismuth titanate (BLT) thin films deposited by sputtering and pulsed laser deposition. Thin Solid Films, 2006, 495, 86-91.	1.8	31
11	Passivation of InP using In(PO3)3â€condensed phosphates: From oxide growth properties to metalâ€insulatorâ€semiconductor fieldâ€effectâ€transistor devices. Journal of Applied Physics, 1992, 71, 2981-2992.	2.5	30
12	Electrical and optical characteristics of indium tin oxide thin films deposited by cathodic sputtering for top emitting organic electroluminescent devices. Materials Science and Engineering C, 2002, 21, 265-271.	7.3	26
13	Deposition of AlN films by reactive sputtering: Effect of radiofrequency substrate bias. Thin Solid Films, 2007, 515, 7105-7108.	1.8	25
14	Mott insulators: A large class of materials for Leaky Integrate and Fire (LIF) artificial neuron. Journal of Applied Physics, 2018, 124, .	2.5	24
15	First evidence of resistive switching in polycrystalline GaV₄S₈ thin layers. Physica Status Solidi - Rapid Research Letters, 2011, 5, 53-55.	2.4	23
16	Raman and XPS studies of CIGS/Mo interfaces under various annealing temperatures. Materials Letters, 2014, 136, 278-281.	2.6	23
17	Investigation of copper indium gallium selenide material growth by selenization of metallic precursors. Journal of Crystal Growth, 2013, 382, 56-60.	1.5	21
18	Impact of the Cu-based substrates and catalyst deposition techniques on carbon nanotube growth at low temperature by PECVD. Microelectronic Engineering, 2007, 84, 2501-2505.	2.4	20

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19	Examination of the electrochemical reactivity of screen printed carbon electrode treated by radio-frequency argon plasma. Electrochemistry Communications, 2007, 9, 1798-1804.	4.7	19
20	Electrical characterizations of resistive random access memory devices based on GaV4S8 thin layers. Thin Solid Films, 2013, 533, 61-65.	1.8	19
21	Control of resistive switching in AM₄Q₈narrow gap Mott insulators: A first step towards neuromorphic applications. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 239-244.	1.8	18
22	Metalâ€“insulator transitions in (V1-xCrx)2O3 thin films deposited by reactive direct current magnetron co-sputtering. Thin Solid Films, 2016, 617, 56-62.	1.8	17
23	In Situ Studies of the Anodic Oxidation of Indium Phosphide. Journal of the Electrochemical Society, 1993, 140, 104-108.	2.9	15
24	Investigation of oxide layer on CdTe film surface and its effect on the device performance. Materials Science in Semiconductor Processing, 2015, 40, 402-406.	4.0	14
25	Studies of CdS/CdTe interface: Comparison of CdS films deposited by close space sublimation and chemical bath deposition techniques. Thin Solid Films, 2015, 582, 290-294.	1.8	13
26	Long-term stability of InP MIS devices. Applied Surface Science, 1991, 50, 383-389.	6.1	12
27	Desorption of ultravioletâ€ozone oxides from InP under phosphorus and arsenic overpressures. Journal of Applied Physics, 1995, 77, 5167-5172.	2.5	12
28	Residual stress control in MoCr thin films deposited by ionized magnetron sputtering. Surface and Coatings Technology, 2006, 200, 6549-6553.	4.8	12
29	Magnetron Sputtering of Aluminium Nitride Thin Films for Thermal Management. Plasma Processes and Polymers, 2007, 4, S1-S5.	3.0	12
30	First demonstration of â€œLeaky Integrate and Fireâ€•artificial neuron behavior on (V0.95Cr0.05)2O3 thin film. MRS Communications, 2018, 8, 835-841.	1.8	11
31	Optimized SiO2/InP structures prepared by electron cyclotron resonance plasma. Journal of Applied Physics, 1996, 80, 3100-3109.	2.5	10
32	Screen-printed carbon electrode modified on its surface with amorphous carbon nitride thin film: Electrochemical and morphological study. Electrochimica Acta, 2007, 52, 5053-5061.	5.2	10
33	Electric Pulse Induced Resistive Switching in the Narrow Gap Mott Insulator GaMo₄S₈. Key Engineering Materials, 2014, 617, 135-140.	0.4	10
34	Surface evolution of sputtered Cu(In,Ga)Se2 thin films under various annealing temperatures. Journal of Materials Science: Materials in Electronics, 2015, 26, 4840-4847.	2.2	10
35	<title>Strength of indium-phosphide-based microstructures</title>. , 1997, 3008, 251.		9
36	Deposition by radio frequency magnetron sputtering of GaV4S8 thin films for resistive random access memory application. Thin Solid Films, 2013, 533, 54-60.	1.8	9

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37	Non-volatile resistive switching in the Mott insulator (V1â^'xCrx)2O3. Physica B: Condensed Matter, 2018, 536, 327-330.	2.7	9
38	Characterizations of CNx thin films made by ionized physical vapor deposition. Thin Solid Films, 2005, 482, 192-196.	1.8	8
39	Influence of Ion Bombardment and Annealing on the Structural and Optical Properties of TiO_x Thin Films Deposited in Inductively Coupled TTIP/O₂ Plasma. Plasma Processes and Polymers, 2009, 6, S741.	3.0	8
40	Investigation of BST thin films deposited by RF magnetron sputtering in pure Argon. Thin Solid Films, 2010, 518, 4619-4622.	1.8	8
41	An optimized Inâ€"CuGa metallic precursors for chalcopyrite thin films. Thin Solid Films, 2013, 545, 251-256.	1.8	8
42	Structural and dielectric characterization of sputtered Tantalum Titanium Oxide thin films for high temperature capacitor applications. Thin Solid Films, 2016, 606, 127-132.	1.8	8
43	2 [micro sign]m resonant cavity enhanced InP/InGaAs single quantum well photo-detector. Electronics Letters, 1999, 35, 1272.	1.0	7
44	A study of different selenium sources in the synthesis processes of chalcopyrite semiconductors. Vacuum, 2014, 105, 46-51.	3.5	7
45	Competition between V2O3 phases deposited by one-step reactive sputtering process on polycrystalline conducting electrode. Thin Solid Films, 2020, 705, 138063.	1.8	7
46	Low temperature plasma carbon nanotubes growth on patterned catalyst. Microelectronic Engineering, 2006, 83, 2427-2431.	2.4	6
47	Correlations Between the Electrical Characteristics of Metalâ€‰â€â€‰Oxideâ€‰â€â€‰InP Tunnel Diodes and the Nature of Thin Interfacial Oxides. Journal of the Electrochemical Society, 1995, 142, 1343-1348.	2.9	5
48	In Situ Photoluminescence Control during Fabrication of SiO2/InP Structures. Journal of the Electrochemical Society, 1997, 144, 2086-2095.	2.9	5
49	Dip-coated La2Ti2O7 as a buffer layer for growth of Bi3.25La0.75Ti3O12 films with enhanced (011) orientation. Journal of the European Ceramic Society, 2009, 29, 1977-1985.	5.7	5
50	Small scale mechanical properties of polycrystalline materials: in situ diffraction studies. International Journal of Nanotechnology, 2008, 5, 609.	0.2	4
51	Investigation of chalcopyrite film growth at various temperatures: analyses from top to the bottom of the thin films. Journal of Materials Science: Materials in Electronics, 2014, 25, 2237-2243.	2.2	3
52	Thin films of binary amorphous Zn-Zr alloys developed by magnetron co-sputtering for the production of degradable coronary stents: A preliminary study. Bioactive Materials, 2018, 3, 385-388.	15.6	3
53	TWO STEP REACTIVE MAGNETRON SPUTTERING OF BLT THIN FILMS. Integrated Ferroelectrics, 2007, 94, 94-104.	0.7	2
54	Electrical Characteristics of TiTaO Thin Films Deposited on SiO2/Si Substrates by Magnetron Sputtering. ECS Solid State Letters, 2013, 2, Q13-Q15.	1.4	2

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55	(Invited) Control of Resistive Switching in Mott Memories Based on TiN/AM4Q8/TiN MIM Devices. ECS Transactions, 2017, 75, 3-12.	0.5	2
56	Control of stoichiometry and morphology in polycrystalline V2O3 thin films using oxygen buffers. Journal of Materials Science, 2020, 55, 14717-14727.	3.7	2
57	An Artificial Neuron Founded on Resistive Switching of Mott Insulators. , 2017, , .		1
58	Mott Memory Devices Based on the Mott Insulator (V1-xCrx)2O3. , 2018, , .		1
59	Sol-gel-deposited Sb-doped SnO 2 as transparent anode for OLED: process, patterning, and hole injection characteristics. , 2002, 4464, 103.		0
60	Comparison of Electrical Behavior of GaN-Based MOS Structures Obtained by Different PECVD Process. Materials Science Forum, 0, 711, 228-232.	0.3	0
61	From Resistive Switching Mechanisms in AM4Q8 Mott Insulators to Mott Memories. , 2015, , .		0